

AMENDMENTS TO THE CLAIMS

1. (Original) A semiconductor apparatus, comprising:
 - a semiconductor substrate;
 - an electrode pad including a metal layer and formed on the semiconductor substrate;
 - a MOS transistor formed on the semiconductor substrate; and
 - an analog circuit formed in a region under the electrode pad on the semiconductor substrate and comprising a resistive element including a semiconductor material.
2. (Original) A semiconductor apparatus according to Claim 1, wherein the resistive element includes a specific material made of one of polysilicon, silicon germanium, and silicon chrome.
3. (Original) A semiconductor apparatus according to Claim 1, wherein the resistive element includes a plurality of resistors.
4. (Currently amended) A semiconductor apparatus according to Claim 1, wherein the MOS transistor comprises a gate electrode including ~~the~~ a specific material of the resistive element.
5. (Original) A semiconductor apparatus according to Claim 1, further comprising:
 - an insulating film formed on the semiconductor substrate in a region in a vicinity of the electrode pad; and
 - a fuse element formed on the insulating film.

6. (Currently amended) A semiconductor apparatus according to Claim 5, wherein the insulating film includes ~~the~~ a specific material of the resistive element.

7. (Previously Presented) A semiconductor apparatus according to Claim 5, further comprising:

a rerouting layer formed in a region above the fuse element; and

an external connection terminal formed on the rerouting layer in a region different from a formation region of the electrode pad.

8. (Original) A semiconductor apparatus according to Claim 5, wherein the analog circuit comprises a voltage setting circuit, the resistive element comprises at least two resistors for producing a split voltage based on an input source power voltage, and the voltage setting circuit changes the split voltage according to a condition of the fuse element.

9. (Original) A semiconductor apparatus according to Claim 1, wherein the resistive element comprises at least two resistors for producing a split voltage based on an input source power voltage, the analog circuit comprises a reference voltage generator for generating a reference voltage and a voltage detector including a comparator for performing a comparison of the split voltage with the reference voltage.

10. (Previously Presented) A semiconductor apparatus according to Claim 9, wherein the analog circuit further comprises an output driver for controlling an output voltage based on an input voltage, and the comparator of the voltage detector outputs a gate control voltage as a result of the comparison for controlling the output driver to control the output voltage.

Claims 11 – 16 (Canceled).

17. (New) A semiconductor apparatus according to Claim 1, wherein the resistive element includes a plurality of doped semiconductor material resistors.

18. (New) A semiconductor apparatus according to Claim 4, wherein said gate electrode has lengthwise ends which are bent in an upward direction towards said electrode pad.